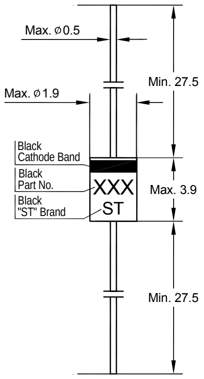
1SS106

SILICON SCHOTTKY BARRIER DIODE

for various detector, high speed switching

Features

- Detection efficiency is very good.
- Small temperature coefficient.
- High reliability with glass seal.



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Average Forward Current	I_O	30	mA
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Electrical Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Current at V_F = 1 V	I_F	4.5	-	mA
Reverse Current at V_R = 6 V	I_R	-	70	µA
Capacitance at V_R = 1 V, f = 1 MHz	C	-	1.5	pF
Rectifier Efficiency at V_{in} = 2 Vrms, f = 40 MHz, R_L = 5 KΩ, C_L = 20 pF	η	70	-	%
ESD Capability [1] at C = 200 pF, both forward and reverse direction 1 pulse.	-	100	-	V

[1] Failure criterion: $I_R \geq 140$ µA at V_R = 6 V

SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company
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ISO/TS 16949 : 2002
Certificate No. 05103

ISO 14001:2004
Certificate No. 7116

ISO 9001:2000
Certificate No. 0506098

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